

1. Global joint venture starts operations as WeEn Semiconductors

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As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

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Thank you for your cooperation and understanding,

WeEn Semiconductors



DISCRETE SEMICONDUCTORS

DATA SHEET

BT151U series CThyristors

Product specification

April 2004



Thyristors

BT151U series C

GENERAL DESCRIPTION

Passivated thyristors in a plastic envelope, intended for use in applications requiring high bidirectional blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

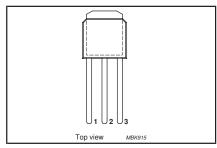
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V _{DRM} , V _{RRM}	BT151U- Repetitive peak off-state voltages Average on-state current RMS on-state current	500C 500 7.5	650C 650 7.5	800C 800 7.5	V A A
IT(RMS) I _{TSM}	Non-repetitive peak on-state current	100	100	100	Ä

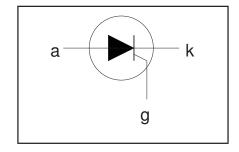
PINNING - SOT533, (I-PAK)

PIN NUMBER	DESCRIPTION
1	cathode
2	anode
3	gate
tab	anode

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT	
V _{DRM} , V _{RRM}	Repetitive peak off-state voltages		-	-500C 500 ¹	-650C 650 ¹	-800C 800	V
I _{T(AV)} I _{T(RMS)} I _{TSM}	Average on-state current RMS on-state current Non-repetitive peak on-state current	half sine wave; $T_{mb} \le 104 ^{\circ}\text{C}$ all conduction angles half sine wave; $T_j = 25 ^{\circ}\text{C}$ prior to surge	- -		7.5 12		A A
l ² t dl _T /dt	I ² t for fusing Repetitive rate of rise of	t = 10 ms t = 8.3 ms t = 10 ms l _{TM} = 20 A; l _G = 50 mA; dl _G /dt = 50 mA/μs	- - -		100 110 50 50		Α Α Α²s Α/μs
I _{GM} V _{RGM} P _{GM} P _{G(AV)} T _{stg} T _i	on-state current after triggering Peak gate current Peak reverse gate voltage Peak gate power Average gate power Storage temperature Junction temperature	over any 20 ms period	- - - -40 -		2 5 5 0.5 150 125		٥°%

¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15 $A/\mu s$.

Thyristors

BT151U series C

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th j-mb}$ $R_{th j-a}$	Thermal resistance junction to mounting base Thermal resistance	in free air	-	- 70	1.3 -	K/W K/W K/W
th j-a	junction to ambient	in nee an		70		10,00

STATIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{GT}	Gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$	-	2	15	mA
l I	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	10	40	mA
l I _H	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	7	20	mA
Ŭ _⊤	On-state voltage	$I_{T} = 23 \text{ A}$	-	1.44	1.75	V
V _{GT}	Gate trigger voltage	$\dot{V}_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}$	-	0.6	1.5	V
		$V_D = V_{DRM(max)}$; $I_T = 0.1 \text{ A}$; $T_j = 125 ^{\circ}\text{C}$	0.25	0.4	-	V
I_D, I_R	Off-state leakage current	$V_D = V_{DRM(max)}$; $V_R = V_{RRM(max)}$; $T_j = 125 ^{\circ}C$	-	0.1	0.5	mA

DYNAMIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV _D /dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% \ V_{DRM(max)}; \ T_j = 125 \ ^{\circ}C;$ exponential waveform $Gate \ open \ circuit$ $R_{GK} = 100 \ \Omega$	50 200	130 1000	- -	V/μs V/μs
t _{gt}	Gate controlled turn-on time Circuit commutated turn-off time	$\begin{array}{l} I_{TM} = 40 \text{ A; } V_D = V_{DRM(max)}; \ I_G = \stackrel{\frown}{0}.1 \text{ A; } \\ dI_G/dt = 5 \text{ A}/\mu s \\ V_D = 67\% \ V_{DRM(max)}; T_j = 125 \ ^{\circ}C; \\ I_{TM} = 20 \text{ A; } V_R = 25 \text{ V; } dI_{TM}/dt = 30 \text{ A}/\mu s; \\ dV_D/dt = 50 \text{ V}/\mu s; \ R_{GK} = 100 \ \Omega \end{array}$	-	70	-	μs μs

Thyristors BT151U series C

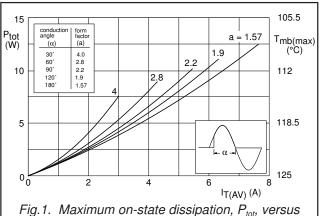


Fig.1. Maximum on-state dissipation, P_{tot} , versus average on-state current, $I_{T(AV)}$, where $a = form \ factor = I_{T(RMS)} / I_{T(AV)}$.

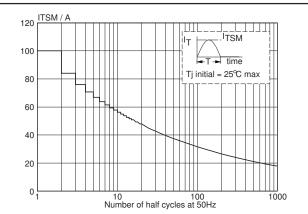


Fig.4. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, f = 50 Hz.

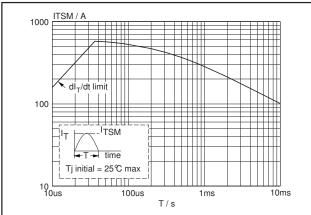


Fig.2. Maximum permissible non-repetitive peak on-state current l_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \le 10$ ms.

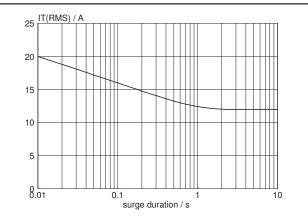


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{mb} \le 100$ °C.

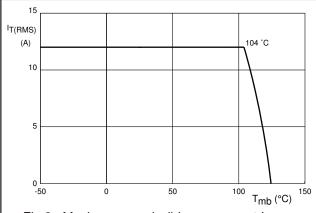
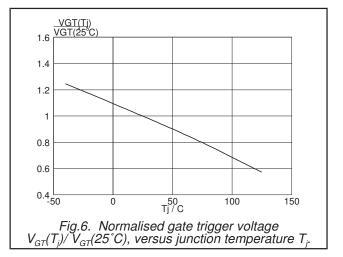
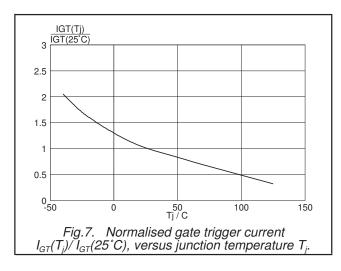
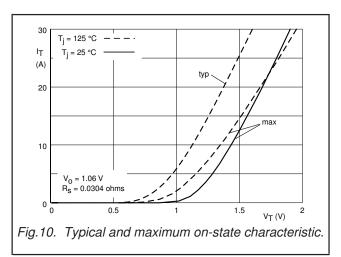


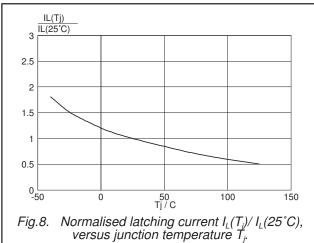
Fig.3. Maximum permissible rms current $I_{T(RMS)}$, versus mounting base temperature T_{mb} .

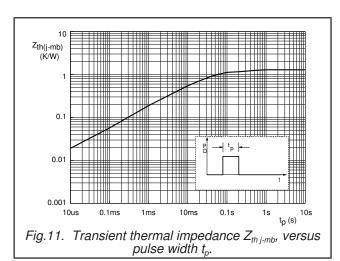


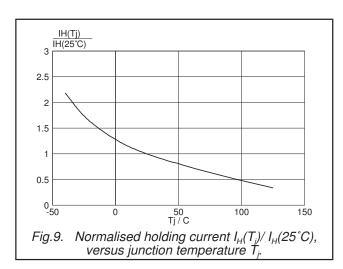
Thyristors BT151U series C

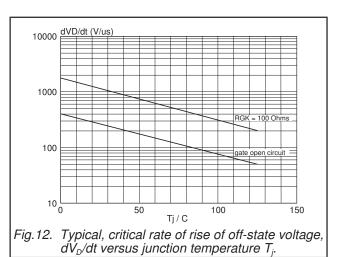












Product specification **NXP Semiconductors**

Thyristors

BT151U series C

MECHANICAL DATA

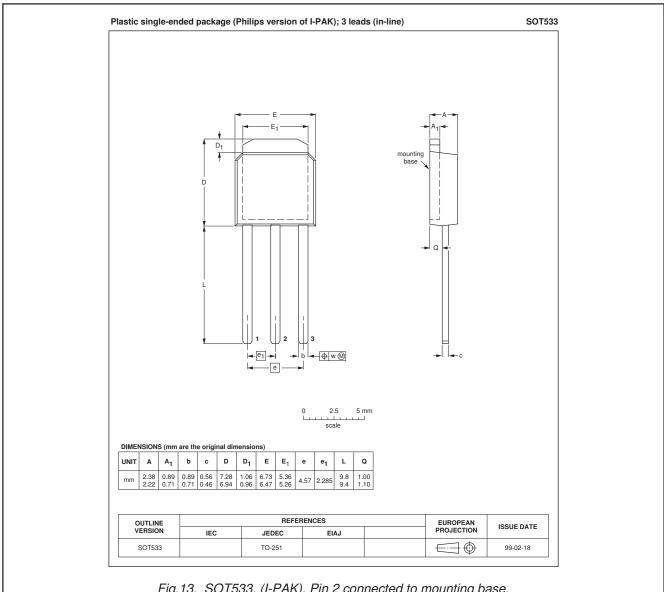


Fig.13. SOT533, (I-PAK). Pin 2 connected to mounting base.

Legal information

DATA SHEET STATUS

DOCUMENT PRODUCT STATUS ⁽¹⁾ STATUS ⁽²⁾		DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet Production		This document contains the product specification.

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